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# PESD36VS2UT

Low capacitance unidirectional double ESD protection diode

Rev. 01 — 16 July 2009

**Product data sheet** 

## 1. Product profile

### 1.1 General description

Low capacitance unidirectional double ElectroStatic Discharge (ESD) protection diode in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package designed to protect up to two signal lines from the damage caused by ESD and other transients.

### **1.2 Features**

- Unidirectional ESD protection of two lines
- Low diode capacitance: C<sub>d</sub> = 17 pF
- Max. peak pulse power: P<sub>PP</sub> = 160 W
- Low clamping voltage: V<sub>CL</sub> = 55 V
- $\blacksquare \quad \text{Ultra low leakage current: } I_{RM} \leq 1 \ \mu\text{A}$

### **1.3 Applications**

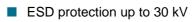
- Computers and peripherals
- Audio and video equipment
- Cellular handsets and accessories
- Subscriber Identity Module (SIM) card protection

### 1.4 Quick reference data

#### Table 1.Quick reference data

 $T_{amb} = 25 \circ C$  unless otherwise specified.

| unio -           | 1                        |                        |     |     |     |      |
|------------------|--------------------------|------------------------|-----|-----|-----|------|
| Symbol           | Parameter                | Conditions             | Min | Тур | Max | Unit |
| Per diode        | 9                        |                        |     |     |     |      |
| V <sub>RWM</sub> | reverse standoff voltage |                        | -   | -   | 36  | V    |
| C <sub>d</sub>   | diode capacitance        | $f = 1 MHz; V_R = 0 V$ | -   | 17  | 35  | pF   |



- IEC 61000-4-2; level 4 (ESD)
- IEC 61000-4-5 (surge); I<sub>PP</sub> = 2.5 A
- AEC-Q101 qualified
- Portable electronics
- Communication systems
- 10/100 Mbit/s Ethernet





### Low capacitance unidirectional double ESD protection diode

## 2. Pinning information

| Table 2. | Pinning           |                    |                |
|----------|-------------------|--------------------|----------------|
| Pin      | Description       | Simplified outline | Graphic symbol |
| 1        | cathode (diode 1) |                    |                |
| 2        | cathode (diode 2) |                    | 3              |
| 3        | common anode      |                    |                |

## 3. Ordering information

| Table 3. Order      | ring informat | ion                                      |         |
|---------------------|---------------|--|---------|
| Type number Package |               |  |         |
|                     | Name          | Description                              | Version |
| PESD36VS2UT         | -             | plastic surface-mounted package; 3 leads | SOT23   |

### 4. Marking

| Type number | Marking code <sup>[1]</sup> |  |
|-------------|-----------------------------|--|
| PESD36VS2UT | LF*                         |  |

- \* = p: made in Hong Kong
- \* = t: made in Malaysia
- \* = W: made in China

## 5. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter            | Conditions               | Min           | Max  | Unit |
|------------------|----------------------|--------------------------|---------------|------|------|
| Per diode        |                      |                          |               |      |      |
| P <sub>PP</sub>  | peak pulse power     | t <sub>p</sub> = 8/20 μs | <u>[1][2]</u> | 160  | W    |
| I <sub>PP</sub>  | peak pulse current   | t <sub>p</sub> = 8/20 μs | <u>[1][2]</u> | 2.5  | А    |
| Per device       |                      |                          |               |      |      |
| Tj               | junction temperature |                          | -             | 150  | °C   |
| T <sub>amb</sub> | ambient temperature  |                          | -55           | +150 | °C   |
| T <sub>stg</sub> | storage temperature  |                          | -65           | +150 | °C   |
|                  |                      |                          |               |      |      |

[1] Non-repetitive current pulse 8/20 µs exponential decay waveform according to IEC 61000-4-5.

[2] Measured from pin 1 or 2 to pin 3.

#### Low capacitance unidirectional double ESD protection diode

#### Table 6.ESD maximum ratings

 $T_{amb} = 25 \circ C$  unless otherwise specified.

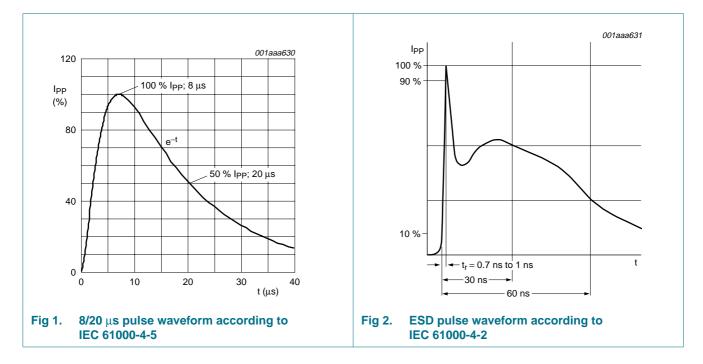
| Symbol   | Parameter                            | Conditions                        |     | Min | Max | Unit |
|--|--------------------------------------|-----------------------------------|-----|-----|-----|------|
| Per diode  | •                                    |                                   |     |     |     |      |
| V <sub>ESD</sub> electrostatic discharge voltage | IEC 61000-4-2<br>(contact discharge) | <u>[1][2]</u>                     | -   | 30  | kV  |      |
|  |                                      | machine model                     | [2] | -   | 400 | V    |
|  |                                      | MIL-STD-883 (human<br>body model) |     | -   | 8   | kV   |

[1] Device stressed with ten non-repetitive ESD pulses.

[2] Measured from pin 1 to pin 2.

#### Table 7. ESD standards compliance

| Standard                                | Conditions                      |
|---|---------------------------------|
| Per diode                               |                                 |
| IEC 61000-4-2; level 4 (ESD)            | > 15 kV (air); > 8 kV (contact) |
| MIL-STD-883; class 3 (human body model) | > 4 kV                          |



### Low capacitance unidirectional double ESD protection diode

## 6. Characteristics

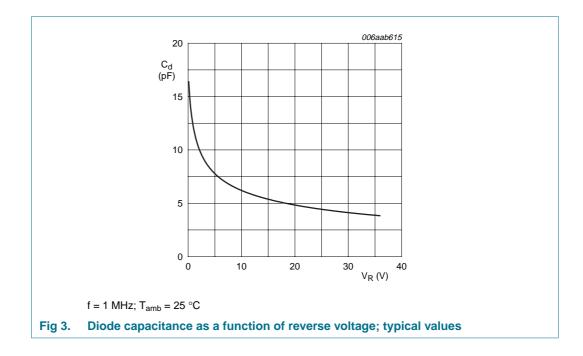
| Table 8 | 8. | Characteristics |
|---------|----|-----------------|
|         |    |                 |

 $T_{amb} = 25 \circ C$  unless otherwise specified.

|                  |                          | ou.                                |              |        |     |      |
|------------------|--------------------------|------------------------------------|--------------|--------|-----|------|
| Symbol           | Parameter                | Conditions                         | Min          | Тур    | Max | Unit |
| Per diode        | )                        |                                    |              |        |     |      |
| V <sub>RWM</sub> | reverse standoff voltage |                                    | -            | -      | 36  | V    |
| I <sub>RM</sub>  | reverse leakage current  | $V_{RWM} = 30 V$                   | -            | < 0.02 | 1   | μA   |
| V <sub>BR</sub>  | breakdown voltage        | I <sub>R</sub> = 5 mA              | 40           | 44     | -   | V    |
| C <sub>d</sub>   | diode capacitance        | f = 1 MHz;<br>V <sub>R</sub> = 0 V | <u>[1]</u> - | 17     | 35  | pF   |
| V <sub>CL</sub>  | clamping voltage         | I <sub>PP</sub> = 1 A              | [1][2] _     | 55     | 60  | V    |
| r <sub>dif</sub> | differential resistance  | I <sub>R</sub> = 0.5 mA            | -            | -      | 300 | Ω    |
|                  |                          |                                    |              |        |     |      |

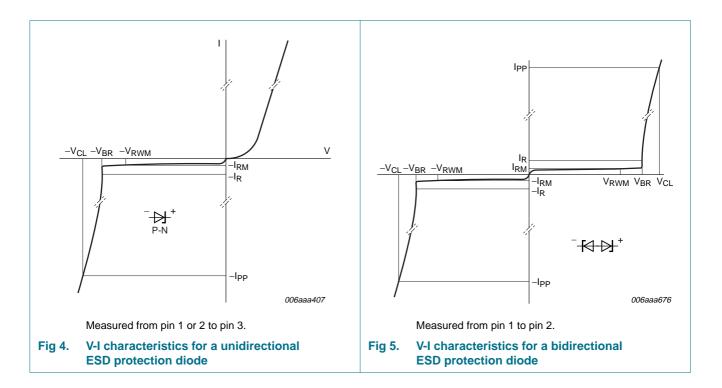
[1] Measured from pin 1 or 2 to pin 3.

[2] Non-repetitive current pulse 8/20 µs exponential decay waveform according to IEC 61000-4-5.



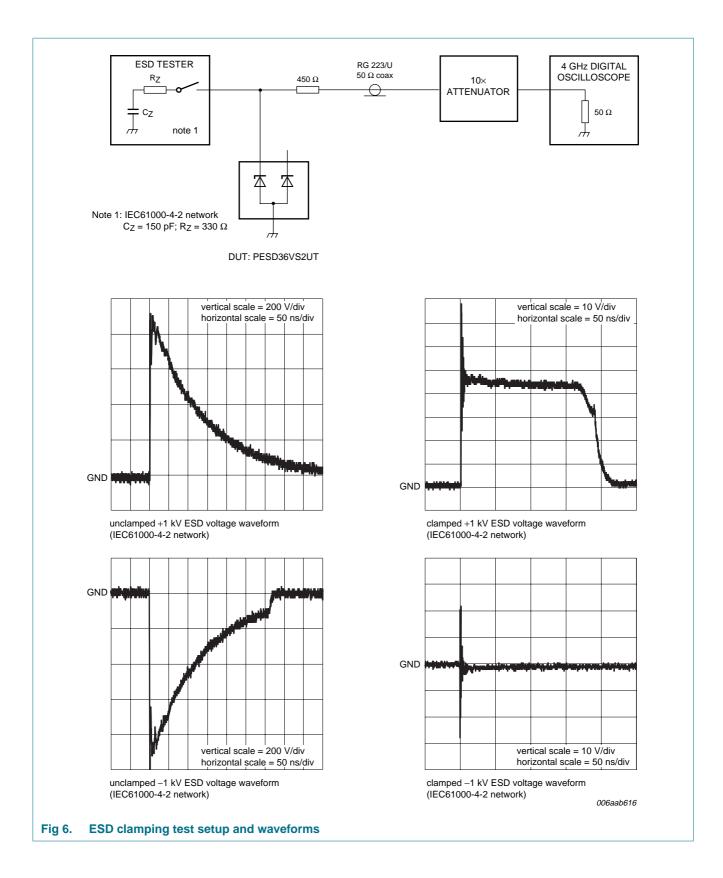


Low capacitance unidirectional double ESD protection diode





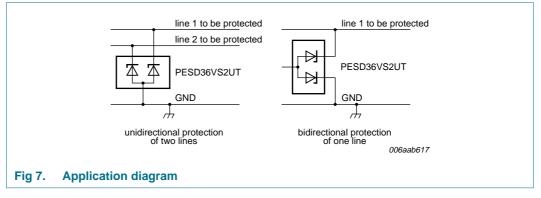
#### Low capacitance unidirectional double ESD protection diode



#### Low capacitance unidirectional double ESD protection diode

## 7. Application information

The PESD36VS2UT is designed for the protection of up to two unidirectional data or signal lines from the damage caused by ESD and surge pulses. The devices may be used on lines where the signal polarities are either positive or negative with respect to ground. The PESD36VS2UT provides a surge capability of 160 W per line for an 8/20  $\mu$ s waveform.



#### Circuit board layout and protection device placement

Circuit board layout is critical for the suppression of ESD, Electrical Fast Transient (EFT) and surge transients. The following guidelines are recommended:

- 1. Place the device as close to the input terminal or connector as possible.
- 2. The path length between the device and the protected line should be minimized.
- 3. Keep parallel signal paths to a minimum.
- 4. Avoid running protected conductors in parallel with unprotected conductors.
- 5. Minimize all Printed-Circuit Board (PCB) conductive loops including power and ground loops.
- 6. Minimize the length of the transient return path to ground.
- 7. Avoid using shared transient return paths to a common ground point.
- 8. Ground planes should be used whenever possible. For multilayer PCBs, use ground vias.

### 8. Test information

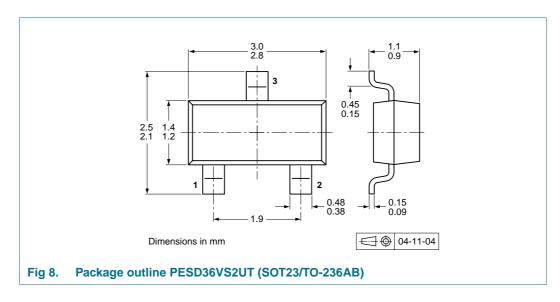
#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.



Low capacitance unidirectional double ESD protection diode

## 9. Package outline



## **10. Packing information**

#### Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

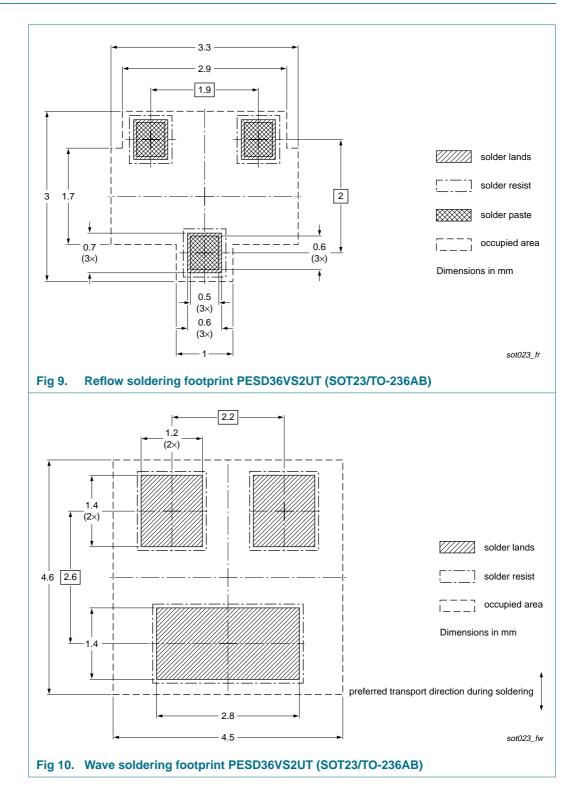
| Type number | Package | Description                    | Packing | quantity |
|-------------|---------|--------------------------------|---------|----------|
|             |         |                                | 3000    | 10000    |
| PESD36VS2UT | SOT23   | 4 mm pitch, 8 mm tape and reel | -215    | -135     |

[1] For further information and the availability of packing methods, see Section 14.



#### Low capacitance unidirectional double ESD protection diode

## **11. Soldering**



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## 12. Revision history

| Table 10.         Revision histor | У            |                    |               |            |
|-----------------------------------|--------------|--------------------|---------------|------------|
| Document ID                       | Release date | Data sheet status  | Change notice | Supersedes |
| PESD36VS2UT_1                     | 20090716     | Product data sheet | -             | -          |

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## **13. Legal information**

### 13.1 Data sheet status

| Document status <sup>[1][2]</sup> | Product status <sup>[3]</sup> | Definition  |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet      | Development                   | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet    | Qualification                 | This document contains data from the preliminary specification.                       |
| Product [short] data sheet        | Production                    | This document contains the product specification.                                     |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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## 14. Contact information

For more information, please visit: http://www.nxp.com

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PESD36VS2UT\_1
Product data sheet



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